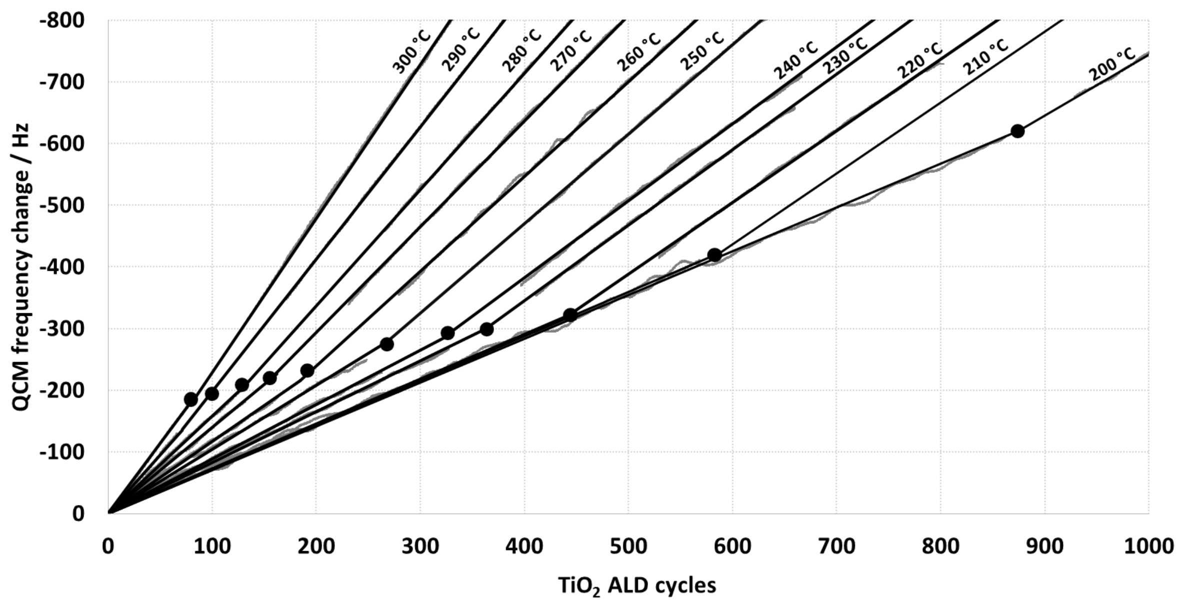

Figure 1 – QCM frequency changes during TiO_2 ALD processes at various substrate temperatures from 200 to 300 °C showing a spontaneous change of the film growth per cycle

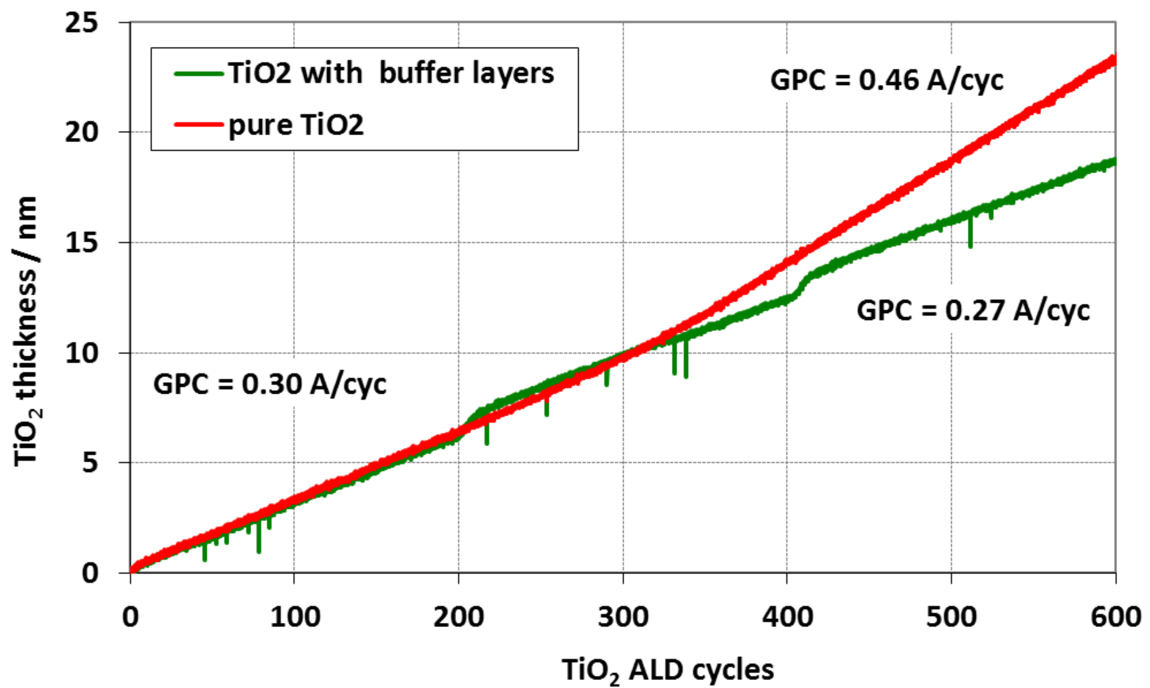

Figure 2 – Effect of Al_2O_3 buffer layers suppressing the TiO_2 crystallization and enabling a constant growth per cycle